12jun02 12:31:20 User267149 Session D139.1

SYSTEM:OS - DIALOG OneSearch

File 344: CHINESE PATENTS ABS APR 1985-2002/APR

(c) 2002 EUROPEAN PATENT OFFICE

File 347: JAPIO Oct 1976-2002/Feb (Updated 020604)

(c) 2002 JPO & JAPIO

\*File 347: JAPIO data problems with year 2000 records are now fixed. Alerts have been run. See HELP NEWS 347 for details. File 351:Derwent WPI 1963-2002/UD,UM &UP=200236

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\*File 351: Please see HELP NEWS 351 for details about U.S. provisional applications.

File 371:French Patents 1961-2002/BOPI 200209

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File 350: Derwent WPIX 1963-2002/UD, UM &UP=200236

(c) 2002 Thomson Derwent

\*File 350: Please see HELP NEWS 350 for details about U.S. provisional applications. Also more updates in 2002.

```
Set
        Items
                Description
         9217
                 (BALL()GRID OR BGA OR LAND()GRID OR PAD()GRID OR PIN()GRID-
S1
             )(3N)ARRAY??
S2
         1233
                INTERCONNECT??????(3N) DENSIT?????
s3
       291265
                INTEGRAT??????(2N) (CIRCUIT??? OR IC)
        51380
                100 (W) (MU OR MICRON? ?)
S4
         1999
                (MU OR MICRON? ?) (3N) (CENTER? ? OR CENTR?????)
S5
S6
         2147
                PITCH???(3N)(MICRON? ? OR MU)
                CENTER? ?(1W)CENTER? ?
S7
         1205
S8
          391
                PITCH???(2N)CENTER? ?
S 9
        56628
                S4:S8
S10
        49770
                ACTIVE (3N) SURFACE? ?
S11
          967
                PASSIVE (3N) SURFACE? ?
S12
      2571127
                ELECTRIC???
S13
       891706
                (COUPL??? OR CONNECT??? OR LINK??? OR JOIN???) (3N) (MEMBER?
             ? OR UNIT? ? OR PART? ?)
                FILM??? OR LAYER??? OR COAT??? OR SUBSTRAT?????
S14
      5123739
      1196023
                INSULAT????? OR MC=U11-C08A6
S15
S16
         1496
                INTERPOSER? ?
                POLYIMIDE? ? OR POLYIMIDO OR RESIN OR EPOX??? OR (HEAT??? -
S17
      2385696
             OR WEAR OR CORROSION???) (4N) RESIST???????
                MC=VO4-R07C
S18
        19896
                IMIDO OR IMIDE???(2N)POLYMER???
S19
S20
        45261
                WIRE? ?(2N)(BOND??? OR BALL? ?)
        45405
                (SOLDER??? OR FUSIBLE(2N)ALLOY? ? OR BOND???? OR JOIN??????
S21
              OR CEMENT????) (5N) (BALL? ? OR BUMP? ?)
S22
         1363
                (COPPER OR CU) (5N) (BALL? ? OR BUMP? ?)
S23
                (NICKEL OR NI) (5N) (BALL? ? OR BUMP? ?)
S24
          140
                (PALLADIUM OR PD) (5N) (BALL? ? OR BUMP? ?)
S25
        68594
                TAPE()AUTOMAT???(1N)BOND??? OR TAB
S26
         8794
                FLIP()CHIP OR FLIP()BOND
                THERMOSETTING? ? OR THERMOPLASTIC???(3N)(BLEND??? OR MIX OR
S27
       117027
              MIXTURE OR MIXING)
S28
         8246
                THERMO() COMPRESSION??? OR THERMOCOMPRESSION??? OR INTERDIF-
             FUSION??? OR INTER()DIFFUSION???
S29
       125008
                S27 OR S28
S30
        62688
                ENCAPSULAT?????? OR CAPSULAT??????
                S1 AND S30
S31
          381
S32
           15
                S31 AND S25
                S32 AND S9
S33
           0
                S32 AND (S17 OR S19)
S34
           12
                (S4 OR S5 OR S6 OR S7) AND S16
S35
           Ω
S36
        20084
                (S4 OR S5 OR S6 OR S7) AND (S17 OR S19)
                MC=V04-R07C
S37
         1274
      2395822
                S17, S19, S37
S38
                MC=U11-E01C
S39
         7018
S40
        12472
                S26,S39
         7018
                S40 AND S39
S41
                S41 AND S30
S42
          166
           20
                S42 AND S15
S43
           0
                S43 AND S16
S44
           12
S45
                S43 AND S3
                IDPAT (sorted in duplicate/non-duplicate order)
S46
           12
S47
            6
                IDPAT (primary/non-duplicate records only)
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12/06/2002 09/992,387
S48
         306
               S9 AND (S10 OR S11)
S49
          21
              S48 AND S15
S50
           0
              S49 AND S16
S51
           2
              S49 AND S20
S52
              S49 AND (S21 OR S22 OR S23 OR S24)
S53
           0
              S49 AND GOLD(3N)(BUMP??? OR BALL???)
           0
              S49 AND S29
S54
S55
          21
              S49 AND S4
S56
          0
              S55 AND S5
          21
S57
               IDPAT S55 (sorted in duplicate/non-duplicate order)
S58
          14
               IDPAT S55 (primary/non-duplicate records only)
S59
         130
               S1 AND S16
S60
          65
               S59 AND S21
S61
          3
               S60 AND S22
S62
        1302
              S29 AND S30
S63
          0
               S62 AND (INTERCONNECT??????(3N) DENSIT?????)
S64
          10
               S62 AND S10
S65
           2
               S64 AND S40
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(Item 1 from file: 351) 34/3, AB/1DIALOG(R) File 351: Derwent WPI (c) 2002 Thomson Derwent. All rts. reserv. 013192417 WPI Acc No: 2000-364290/200031 XRAM Acc No: C00-109842 XRPX Acc No: N00-272620 Integrated circuit package e.g. ball grid array package has flex tape which has conductive metal lead pattern positioned on side of tape facing substrate with apertures, exposes lead pattern for solder ball bonding Patent Assignee: LSI LOGIC CORP (LSIL-N) Inventor: ALAGARATNAM M; CHIA C J; LOW Q H Number of Countries: 001 Number of Patents: 001 Patent Family: Applicat No Patent No Week Kind Date Kind Date 20000502 US 97842379 US 6057594 Α 19970423 200031 B Α Priority Applications (No Type Date): US 97842379 A 19970423 Patent Details: Patent No Kind Lan Pg Main IPC Filing Notes US 6057594 Α 5 H01L-023/495 Abstract (Basic): US 6057594 A Abstract (Basic): NOVELTY - IC package has molded plastic base structure sandwiched between heat conductive substrate (4) and flex tape (16). Flex tape has conductive metal lead pattern (18) positioned on tape side facing substrate with apertures (22) that exposes lead pattern for solder ball bonding. Semiconductor IC (12) is mounted on central point of heat spreader (10). Chip and wiring bonding are then encapsulated on DETAILED DESCRIPTION - A molded plastic base structure includes heat conductive substrate and flex tape extending from corresponding side of substrate. The heat conductive substrate is laminate structure comprising metal and ceramics. The molded plastic material is present between substrate and flex tape which has conductive metal lead pattern on the tape side which faces the substrate. Apertures exposes conductive lead pattern for solder ball bonding. A semiconductor IC chip with active and non-active side is mounted to central portion of heat spreader and active side has bond pads (14) for interconnecting integrated circuit. Wire bonding interconnects bond pads on clip to metal lead pattern chip. The wire bonding are then encapsulated on substrate by filling cavity in the substrate partially by a resin. The cavity has molded plastic along its side walls. The flex tape also extends along side walls of cavity. USE - For large scale integrated (LSI) circuits, integrated circuit (IC) packages e.g. ball grid array (BGA)

ADVANTAGE - As chip is directly fixed to heat spreader heat dissipation is increased. Wire bonding is lower in cost and has

package, formed by tape automated bonding (TAB

flexibility higher then tape automated bonding (

TAB) hence resulting package is economical to manufacture, thin
and light weight.
 DESCRIPTION OF DRAWING(S) - The figure shows perspective view of
ball grid array package.
 Heat conductive substrate (4)
 Heat spreader (10)
 Semiconductor integrated chip (12)
 Bond pads (14)
 Flex tape (16)

34/3,AB/2 (Item 2 from file: 351) DIALOG(R)File 351:Derwent WPI (c) 2002 Thomson Derwent. All rts. reserv. 012180204 WPI Acc No: 1998-597117/199851

XRAM Acc No: C98-179352 XRPX Acc No: N98-464724

Thin power tape ball grid array package - has

semiconductor chip mounted in heat spreader recess and its bonding pads

connected to metal interconnect patterns on flex tape

Patent Assignee: LSI LOGIC CORP (LSIL-N) Inventor: ALAGARATNAM M; CHIA C J; VARIOT P Number of Countries: 027 Number of Patents: 003 Patent Family:

Applicat No Kind Patent No Kind Date Date EP 880175 A2 19981125 EP 98303039 19980421 199851 Α JP 11003957 19990106 JP 98109632 Α 19980420 199911 Α US 5869889 Α 19990209 US 97840614 Α 19970421 199913

Priority Applications (No Type Date): US 97840614 A 19970421

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

EP 880175 A2 E 5 H01L-023/13

Designated States (Regional): AL AT BE CH CY DE DK ES FI FR GB GR IE IT

LI LT LU LV MC MK NL PT RO SE SI JP 11003957 Α 4 H01L-023/12 US 5869889 H01L-023/34 Α

Abstract (Basic): EP 880175 A

Package comprises a heat conductive support (10) formed to have a recessed portion with opposing planar surfaces (12,14) and a centrally disposed surface (16). Flex tape is attached to the planar surfaces (12,14) and extends to the centrally disposed surface (16). The flex tape includes one or more metal interconnect patterns (22) on an exposed surface. Semiconductor integrated circuit chip (24) is mounted on centrally disposed surface (16) spaced from the flex tape (18,20). Chip (24) has bonding pads (26). Wire bonds interconnect pads (26) to the interconnect pattern (22). Preferably chip (24) and the wire bonds are encapsulated by plastic molding or epoxy on the heat conductive support (10). Preferably the metal interconnect pattern (22) is connected by solder balls to a mother board.

USE - Flex tape ball grid array package where the flex tape and a formed heat spreader provide the package substrate. ADVANTAGE - The use of flex tape for the substrate is cheaper to manufacture than laminates and ceramics and the wire bonding for the interconnect of the chip and the substrate is lower in cost has higher flexibility than other interconnects such as TAB bonding. The recess or cavity for attachment of the chip to the heat spreader allows for greater protection of the chip and easier assembly of a thin and light package.

34/3,AB/3 (Item 3 from file: 351) DIALOG(R)File 351:Derwent WPI (c) 2002 Thomson Derwent. All rts. reserv.

011556346

WPI Acc No: 1997-532827/199749

XRAM Acc No: C97-170101 XRPX Acc No: N97-443738

Liquid resin encapsulant for encapsulating semiconductor devices - based on naphthalene polyepoxy resin, hardener and

silica powder

Patent Assignee: TOSHIBA CHEM CORP (TOSM )

Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No Kind Date Applicat No Kind Date Week
JP 9255763 A 19970930 JP 9693600 A 19960322 199749 B

Priority Applications (No Type Date): JP 9693600 A 19960322

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

JP 9255763 A 4 C08G-059/24

Abstract (Basic): JP 9255763 A

An encapsulated semiconductor device comprises a device which is encapsulated with a cured substance of a liquid resin encapsulant consisting of (A) an epoxy resin containing a naphthalene skeleton, (B) a hardener, and (C) a silica powder.

Also claimed is a liquid **resin** encapsulant which comprises essential components of (A) an **epoxy resin** containing naphthalene skeleton, (B) a hardener, and (C) a silica powder.

USE - This is used in PPGA (plastic pin grid

array) and TAB (tape automated bonding).

ADVANTAGE - This encapsulant has good adhesion, moisture resistance, heat resistance, electric properties, and workability such as flowability, and no occurrence of voids and cracks, giving a device having little warp and high reliability.

34/3,AB/4 (Item 4 from file: 351) DIALOG(R)File 351:Derwent WPI

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010581359

WPI Acc No: 1996-078312/199609

XRAM Acc No: C96-025943 XRPX Acc No: N96-065175

PCB mounting applications of an **encapsulated** semiconductor package - comprises IC, connection leads and conducting layer sealed in thin layer of waterproof, moulded **resin** that has only solder bumps or other types of appropriate connectors for device mounting showing.

Patent Assignee: MITSUBISHI DENKI KK (MITQ ); MITSUBISHI ELECTRIC CORP

(MITQ )

Inventor: UEDA T

Number of Countries: 003 Number of Patents: 003

Patent Family:

Patent No Kind Applicat No Kind Date Date DE 19526511 A1 19960125 DE 1026511 Α 19950720 199609 B JP 8037253 19960206 JP 94171020 Α 19940722 199615 Α KR 201168 В1 19990615 KR 9522303 Α 19950722 200060

Priority Applications (No Type Date): JP 94171020 A 19940722

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

DE 19526511 A1 32 H01L-023/50 JP 8037253 A 22 H01L-023/12 KR 201168 B1 H01L-023/04

Abstract (Basic): DE 19526511 A

For a device (1) configured for surface mounting the IC (2), connecting pads (3), and the interconnecting leads (4) joined to the pads are all within the surface of the **resin** (6) with only the solder bumps (5) that are connected to the leads (4) showing through the surface of the mould. The **resin encapsulation** may also be used for devices configured for bump-grid **array** (**BGA**), zig=zag or ZIP, SVP or other PCB mounting methods, in each case only the appropriate device supports and connectors being accessible outside the **resin** mould for reflow soldering to the PCB surface. The method may also be used with **TAB** IC's.

 $\ensuremath{\mathsf{USE}}$  - The device may be used in a wide range of manufacturing and PCB mounting applications.

ADVANTAGE - Gives high packing density, reliability and excellent damp resistance and protection from external effects.

(Item 5 from file: 351) 34/3, AB/5DIALOG(R) File 351: Derwent WPI (c) 2002 Thomson Derwent. All rts. reserv. 008100608 WPI Acc No: 1989-365720/198950 XRAM Acc No: C89-162127 XRPX Acc No: N89-278201 Controlling distribution of curable resin on substrate - by forming dam of cured resin using predetermined radiation pattern Patent Assignee: DOW CORNING CORP (DOWO ) Inventor: ECKSTEIN M H; LUTZ M A Number of Countries: 011 Number of Patents: 009 Patent Family: Patent No Kind Date Applicat No Kind Date Week EP 345979 19891213 EP 89305369 Α 19890526 198950 B Α AU 8936144 Α 19891214 199005 BR 8902723 Α 19900123 199009 JP 2017975 JP 89131724 19890526 199009 Α 19900122 Α ES 2014652 Α 19900716 ES 89890201 Α 19890608 199033 US 4961886 Α 19901009 US 88204436 Α 19880609 199043 EP 345979 B1 19940608 EP 89305369 Α 19890526 199422 DE 68915860 19940714 DE 615860 Α 19890526 199428 E EP 89305369 Α 19890526 CA 1336702 C 19950815 CA 599781 Α 19890516 199542 Priority Applications (No Type Date): US 88204436 A 19880609 Patent Details: Main IPC Patent No Kind Lan Pg Filing Notes EP 345979 A E 11 Designated States (Regional): DE FR GB IT NL B1 E 11 B29C-041/36 Designated States (Regional): DE FR GB IT NL DE 68915860 B29C-041/36 Based on patent EP 345979 F.

# Abstract (Basic): EP 345979 A

С

CA 1336702

Flow of a flowable radiation curable material (26) is restricted by forming a dam (40) of the material by exposing a portion of it to radiation of sufficient intensity to cause it to cure.

The flowable material is dispensed onto a substrate and a predetermined area of the substrate is exposed to radiation to form a dam of cured material before the remainder of the material is exposed to the same radiation to cure it.

USE/ADVANTAGE - Process is used to make plastic bosses on substrates and can be used to coat and/or encapsulate printed circuit boards, plastic pin grid arrays, tape automated bonding devices, hybrid circuit substrates, chip on board encapsulation, and encapsulation of devices contg. holes which are to remain free of material.

B29C-041/36

34/3,AB/6 (Item 6 from file: 351) DIALOG(R)File 351:Derwent WPI (c) 2002 Thomson Derwent. All rts. reserv.

007615995

WPI Acc No: 1988-249927/198835

XRPX Acc No: N88-190365

Integrated circuit plastic pin grid array mfg. process

- inserting terminal pins into holes in interconnect tape, and moulding

in encapsulant resin

Patent Assignee: OLIN CORP (OLIN )

Inventor: ARMER T A; BRIDGES W G; CHANG K; CHANG K S
Number of Countries: 032 Number of Patents: 009

Patent Family:

Patent No	Kind	Date	Apı	plicat No	Kind	Date	Week	
WO 8806395	Α	19880825	WO	88US384	Α	19880210	198835	В
AU 8812989	Α	19880914					198849	
US 4816426	Α	19890328	US	8752327	Α	19870521	198915	
EP 382714	Α	19900822	ΕP	88902047	Α	19880210	199034	
JP 2502322	W	19900726	JP	88501929	Α	19880210	199036	
US 4965227	Α	19901023	US	88145977	Α	19880202	199045	
US 5144412	Α	19920901	US	8716614	Α	19870219	199238	
			US	8752327	Α	19870521		
			US	88145977	Α	19880202		
			US	90562281	Α	19900802		
PH 28943	Α	19950613	PH	36494	Α	19880212	199902	
KR 9610011	B1	19960725	WO	88US384	Α	19880210	199922	
			KR	88701166	Α	19880924		

Priority Applications (No Type Date): US 88145977 A 19880202; US 8716614 A 19870219; US 8752327 A 19870521; US 90562281 A 19900802

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes US 4816426 21 Α US 4965227 Α US 5144412 Α 37 H01L-023/02 CIP of application US 8716614 CIP of application US 8752327 Div ex application US 88145977 CIP of patent US 4816426 Div ex patent US 4965227

Abstract (Basic): WO 8806395 A

The interconnect tape (18') with pins (26a) inserted is encapsulated in a body (270) of polymeric resin. Pref. of the outer surface (272) is occupied by the heat sink (106) with a base (247) exposed flush with the surface or raised or recessed. After removal from the mould, the package receives a semiconductor chip )82) attached (273) to the interior base (245) of the heat sink (106) and wire-bonded or connected by tape automated bonding to leads (21).

The enclosure (278) is sealed by a lid (276) with an adhesive or solder ring (280). The tape (18') is supported on shoulders (39') and the collar (108) of the heat sink.

ADVANTAGE - Package can be mfd. with efficiently operated

automated assembly, and single moulding step, prior to which TAB tape with chip attached can be tested.

Abstract (Equivalent): US 5144412 A

Pin grid array package for housing an integrated circuit comprises an interconnect tape defining a metal interconnect circuit pattern, and holes in the pattern into each of which a terminal pin is inserted. The pin heads are slightly larger than the holes to mechanically lock the tape. A polymer resin, e.g. polyphenylsulphide, polysulphone, polyethersulphone, polyarylether, polyamide, polyether ketone or polyetherimide, encapsulates each head.

ADVANTAGE - Low cost automatic assembly. US 4965227 A

The process for forming an integrated circuit **pin grid array** package, comprises the steps of providing an interconnect
tape having first and second opposing surfaces, the first surface
having a metal circuit pattern defining a number of leads forming a set
of holes of a first diameter in the metal circuit pattern. The
insertion end of a pin is inserted into a first fixture. Interconnect
tape is placed over the pin head end such that the holes in the circuit
pattern encircle the pin heads and be the interconnect tape rests on
the first shoulder of the pins. Pins are soldered to the interconnect
tape using a mask to control the solder.

The cavity is filled with a polymer **resin** so as to at least partially surround and support the pins and tape and thereby form the plastic **encapsulated pin grid** 

47/3,AB/1 (Item 1 from file: 350) DIALOG(R)File 350:Derwent WPIX (c) 2002 Thomson Derwent. All rts. reserv.

014416194

WPI Acc No: 2002-236897/200229 Related WPI Acc No: 2002-224860

XRAM Acc No: C02-071629 XRPX Acc No: N02-182211

Method of making integrated circuit package comprises forming die pad and leads on substrate having apertures, mounting integrated circuit device on die pad, connecting device to leads with bond wires and encapsulating bond wires and device

Patent Assignee: AMKOR TECHNOLOGY INC (AMKO-N) Inventor: DARVEAUX R F; FUSARO J M; RODRIGUEZ P Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No Kind Date Applicat No Kind Date Week
US 6331451 B1 20011218 US 99434546 A 19991105 200229 B

Priority Applications (No Type Date): US 99434546 A 19991105 Patent Details:

Patent No Kind Lan Pg Main IPC

US 6331451 B1 21 H01L-021/58

Abstract (Basic): US 6331451 B1

Abstract (Basic):

NOVELTY - Method of making integrated circuit package comprises: forming planar metal die pad and metal leads on insulating substrate having apertures; mounting an integrated circuit device on the die pad; connecting the integrated circuit device to the leads with bond wires; and applying an encapsulant to cover the bond wires and integrated circuit device and fill the apertures.

DETAILED DESCRIPTION - Method of making integrated circuit package involves providing a planar insulative substrate having first apertures (32) between its first and second surfaces. A planar metal die pad (11) and planar metal leads (14, 14A) are arranged on the second surface of the substrate. The first surfaces of the die pads and leads are on the second surface of the substrate and the first apertures are juxtaposed with the first surface of a lead. An integrated circuit device (22) is mounted adjacent the first surface of the die pad. Bond wires (24) are conductively connected between the integrated circuit device and the first surface of a lead through the first aperture juxtaposed with that respective lead. An encapsulant material is applied onto the first surface of the substrate so as to cover the bond wires and the integrated circuit device and fill the first apertures so that the second surfaces of the die pad, leads, and substrate are exposed at a first surface of the package.

Filing Notes

INDEPENDENT CLAIMS are also included for the following:

- (i) a method of making a number of integrated circuit packages;
- (ii) a method of making a flip chip integrated circuit package;

(iii) a method of making a substrate for making an integrated circuit package; and

(iv) a method of making a substrate for making a flip chip integrated circuit package.

USE - None given.

ADVANTAGE - The integrated circuit packages are thinner than conventional packages and have improved thermal performance. The packages and the substrates and the methods of making them are reliable and cost effective because the substrate and packages can be assembled using conventional materials and equipment.

DESCRIPTION OF DRAWING(S) - The drawings illustrate cross-sectional side views of stages of making the package.

Die pad (11)

Lead (14, 14A)

Integrated circuit device (22)

Bond pad (23)

47/3,AB/2 (Item 2 from file: 350)
DIALOG(R)File 350:Derwent WPIX
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013796913

WPI Acc No: 2001-281125/200129 Related WPI Acc No: 2001-272598

XRAM Acc No: C01-085410 XRPX Acc No: N01-200441

Semiconductor and flip chip packages, uses

thermo-electrically conductive epoxy resin to connect bond pad to

backside of die

Patent Assignee: MINCO TECHNOLOGIES LABS INC (MINC-N)

Inventor: POTTER D R; RODENBECK L R

Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No Kind Date Applicat No Kind Date Week
US 20010000927 A1 20010510 US 9865677 A 19980423 200129 B
US 2000739071 A 20001218

Priority Applications (No Type Date): US 9865677 A 19980423; US 2000739071 A 20001218

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

US 20010000927 A1 9 H01L-023/48 Div ex application US 9865677 Div ex patent US 6191487

Abstract (Basic): US 20010000927 A1 Abstract (Basic):

NOVELTY - A via (22) electrically connects the terminal and the contact pad (21) on the external (19) and internal (17) sides of the substrate (18) respectively. A die (12) is positioned so that its front side faces the substrate external side. A metallisation layer (26) is formed on the back side (28) of the die. A bond pad (16) between the die and substrate mates with the contact pad. A conductive substance (20) connects the die back side to the bond pad to form an electrical connection from the die back side to the substrate terminal.

DETAILED DESCRIPTION - INDEPENDENT CLAIMS are also included for the manufacture of a **flip chip** package, a semiconductor chip package, and the manufacture of a semiconductor package.

USE - Manufacturing and connecting semiconductor and **flip chip** packages to printed circuit boards using a back side connection.

ADVANTAGE - The area required for both discrete devices and integrated circuits formed from a standard die having back side connections is reduced. There is no need for lead wires extending from the die in a flip chip package to the printed circuit board so reducing the space require to connect the device to the remainder of the circuit.

DESCRIPTION OF DRAWING(S) - The drawing shows a side cross-section of the **flip chip** package.

Die (12)
Potting material (14)
Bond pad (16)

Internal sides of the substrate (17)
Substrate (18)
External side of the substrate (19)
Conductive substance (20)
Contact pad (21)
Via (22)
Solder balls (24)

Solder balls (24)
Metallisation (26)
Back side of the die (28)

47/3,AB/3 (Item 3 from file: 350)

DIALOG(R) File 350: Derwent WPIX

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012890963

WPI Acc No: 2000-062797/200005 Related WPI Acc No: 1999-633333

XRPX Acc No: N00-049142

Radio frequency (RF) shield structure of integrated circuit

chip package

Patent Assignee: AMKOR TECHNOLOGY INC (AMKO-N)

Inventor: GLENN T P

Number of Countries: 023 Number of Patents: 002

Patent Family:

Patent No Kind Date Applicat No Kind Date WO 9962119 A1 19991202 WO 99US10852 Α 19990517 200005 B US 6150193 Α 20001121 US 96741797 Α 19961031 US 9883524 Α 19980522

Priority Applications (No Type Date): US 9883524 A 19980522; US 96741797 A 19961031

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

WO 9962119 A1 E 48 H01L-023/552

Designated States (National): CA JP KR SG

Designated States (Regional): AT BE CH CY DE DK ES FI FR GB GR IE IT LU

MC NL PT SE

US 6150193 A H01L-021/44 CIP of application US 96741797 CIP of patent US 5981314

Abstract (Basic): WO 9962119 A1

Abstract (Basic):

NOVELTY - The package (10B) has a polymer based insulating encapsulant layer (42) to enclose an IC chip (30) and the upper surface (18) of an insulating substrate (12) in which the IC chip is mounted. An electrically conductive shield layer (150) is formed above the encapsulant layer so that the edges (152,43) of the shield layer and the encapsulant layer are coincident with the edges (46) of insulated substrate.

DETAILED DESCRIPTION - The shield layer comprises polymer containing electrically conductive filler. The bonding pads (38) of the IC chip are connected with the respective metallic traces (22) on the upper surface of the **insulated** substrate through the bonding wires (40). The IC chip is attached to the **insulating** substrate through a **flip chip** interconnection. The metallic layer on the **insulated** substrate is connected to an external reference voltage. An INDEPENDENT CLAIM is also included for shield structure manufacturing method.

USE - In integrated circuit chip package used in electronic devices.

ADVANTAGE - Prevents external radiation from interacting with chip operation. Prevents radiation emission from package that could interfere with other circuit components.

DESCRIPTION OF DRAWING(S) - The figure shows a cross sectional view

of package.
Package (10B)
Insulating substrate (12)
Upper surface (18)
Metallic traces (22)
IC chip (30)
Bonding pads (38)
Bonding wires (40)
Encapsulated layer (42)
Edges of encapsulated layer (43)
Edges of insulated substrate (46)
Shield layer (150)

47/3,AB/4 (Item 4 from file: 350) DIALOG(R)File 350:Derwent WPIX

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#### 012228724

WPI Acc No: 1999-034831/199903

XRAM Acc No: C99-010586 XRPX Acc No: N99-026009

Method of electrical component packaging used at wafer level - by forming

a plurality of posts on a substrate active side and depositing a conductive layer to connect each post to a component contact

Patent Assignee: CHIPSCALE INC (CHIP-N)

Inventor: CHEN C; YOUNG J L

Number of Countries: 082 Number of Patents: 005

Patent Family:

n	hant Na	T2 1 1	D - + -	70	- 7	TZ 2	D-+-	T-7 1.	
Pa	tent No	Kind	Date	App	olicat No	Kind	Date	Week	
WO	9852225	A1	19981119	WO	98US9793	A	19980513	199903	В
ΑU	9873856	A	19981208	ΑU	9873856	A	19980513	199916	
GB	2341277	A	20000308	WO	98US9793	A	19980513	200015	
				GB	9926807	A	19991115		
US	6051489	Α	20000418	US	97855106	A	19970513	200026	
KR	2001012499	A	20010215	KR	99710454	A	19991112	200154	

Priority Applications (No Type Date): US 97855106 A 19970513

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

US 6051489 A H01L-021/44

Abstract (Basic): WO 9852225 A

A method (I) for making an electronic component package from a component with a number of contact areas on an active side of a substrate comprises: (a) forming a plurality of posts on the active side; (b) depositing a conductive layer for electrically coupling each contact area to its respective post and for contracting traces on a printed circuit board.

Also claimed is an alternative method to (I) comprising: (a) depositing gold beams over the contacts; (b) depositing a first insulating layer over the component covering the beams; (c) coupling a cap to the component covering the insulating layer; (d) patterning the cap to form a number of trenches thus defining a number of posts and a centre area and exposing the insulating layer over the metal beams; (e) depositing a second insulating layer over the component covering the posts and centre area; (f) etching all layers above the beams to at least partially expose them; and (g) depositing a conductive layer over the posts to electrically connect the beams and posts.

Also claimed is a package made according to (I).

USE - Used for electronic component packaging, particularly wafer level processing.

ADVANTAGE - The invention provides a circuit package manufacturable at wafer level which provides flexibility and compliancy. Lead connection size can be tailored to the required purpose and lead connections are not on the die surface thus allowing smaller bond pads/junction areas and minimising stress at the surface. The package

may be encapsulated to protect the circuit and an
integrated heat sink may be provide

47/3, AB/5 (Item 5 from file: 350)

DIALOG(R) File 350: Derwent WPIX

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012191657

WPI Acc No: 1998-608570/199851 Related WPI Acc No: 1997-098910

XRPX Acc No: N98-473305

Integrated circuit packaging method - uses flipchip bonding to attach first wafer having tin solder bumps to second wafer having gold ball bumps followed by resin encapsulation and subjects portions of lead fingers exposed from package to final processing step

Patent Assignee: LEI W (LEIW-I)

Inventor: LEI W

Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No Kind Date Applicat No Kind Date Week
TW 338838 A 19980821 TW 95107022 A 19970704 199851 B

Priority Applications (No Type Date): TW 95107022 A 19970704

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

TW 338838 A 18 H01L-021/60

Abstract (Basic): TW 338838 A

The method involves forming a lead frame having inner and outer layers by using a through punching technique with the outer layer having several conductive lead fingers and inner layer being used for putting a first wafer on a substrate. The first end edge of the lead finger is extended directionally to the substrate, and the second end edge is located along an opposing direction of the first end edge and all extended outwardly.

The surface of the first wafer has several conductive sheets and tin soldering bumps, covered by an insulating layer with flip chip bonding used to place a second wafer having several gold ball bumps such that it faces the tin soldering bumps of the first wafer. The gold ball bumps of the second wafer are secured to corresponding tin soldering bumps on the first wafer. Metal leads are bonded to connect the conductive sheet and the lead finger, for providing a conductive path from the first wafer and an outer circuit followed by resin encapsulation. Outer portions of the lead fingers are exposed from the package and are subjected to a final processing step to finish the packing procedure.

Dwg.0/3

47/3,AB/6 (Item 6 from file: 350) DIALOG(R)File 350:Derwent WPIX (c) 2002 Thomson Derwent. All rts. reserv.

011668768

WPI Acc No: 1998-085677/199808

XRAM Acc No: C98-028921 XRPX Acc No: N98-068060

Attaching integrated circuit component with solder bumps to substrate with bond pads - using anhydride containing flux such as

methyl- hexahydro-phthalic anhydride
Patent Assignee: MOTOROLA INC (MOTI )

Inventor: GAMOTA D R; HERTSBERG M; SCHEIFERS S M; WILLE S L

Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No Kind Date Applicat No Kind Date Week
US 5704116 A 19980106 US 96642708 A 19960503 199808 B

Priority Applications (No Type Date): US 96642708 A 19960503

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

US 5704116 A 5 H05K-003/34

Abstract (Basic): US 5704116 A

A method for attaching an integrated circuit component having solder bumps to a substrate having bond pads comprises: (a) dispensing onto the bond pads a solution containing an anhydride fluxing agent; (b) superposing the integrated circuit component onto the substrate so that each of the solder bump rests against one of the bond pads and is held by the fluxing agent; and (c) heating to bond the solder bumps to the bond pads and to vaporise the anhydride compound.

Also claimed is an encapsulant method for attaching an integrated circuit component to a substrate.

USE - The process is useful for mounting integrated circuits, e.g. on printed circuit boards (especially FR4 board which is formed of a polymer layer laminated onto a ceramic or polymer/glass mesh core) using the flip-chip process or a ball grid array package onto bond pads, e.g. made of aluminium coated with a layer of chromium covered with copper.

ADVANTAGE - The anhydride can be vaporised during reflow of the solder bump interconnections, leaving no residue on the board which may interfere with under-filling of the component with a polymeric encapsulant. However, if any anhydride residue remains on the surface of the substrate, it can be readily solubilised into the encapsulant which includes an anhydride hardener similar to the anhydride in the fluxing agent. The substrate surface does not need to be cleaned prior to encapsulation and good encapsulation adhesion is achieved by incorporating any anhydride residue into the encapsulant. Anhydride fluxing agents provide more reliable connection than those containing acids, since anhydrides are more dielectric than acids and lead to better insulation and a lower chance of shorts between leads on the substrate.

51/3,AB/1 (Item 1 from file: 347) DIALOG(R)File 347:JAPIO

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01836249

MANUFACTURE OF SEMICONDUCTOR DEVICE

PUB. NO.: 61-050349 [JP 61050349 A] PUBLISHED: March 12, 1986 (19860312)

INVENTOR(s): NITTA TAKEHISA
OGIUE KATSUMI
OTSUKA KANJI
ONISHI SHINJI

APPLICANT(s): HITACHI LTD [000510] (A Japanese Company or Corporation), JP

(Japan)

APPL. NO.: 60-161860 [JP 85161860] FILED: July 24, 1985 (19850724)

JOURNAL: Section: E, Section No. 421, Vol. 10, No. 209, Pg. 129, July

22, 1986 (19860722)

# ABSTRACT

PURPOSE: To prevent any erroneous operation due to .alpha. ray irradiation from happening by a method wherein a semiconductor chip is bonded on a substrate and then multiple electrodes on the chip are connected to corresponding external conductive means simultaneously bonding .alpha. ray shielding sheet on the **surface** of **active** region of semiconductor chip.

CONSTITUTION: A semiconductor chip 14 is bonded on the surface of ceramics—made insulating base 10 through the intermediary of an adhesive layer 13 made of Au foil or Au metallized layer while multiple electrodes are electrically connected to corresponding leads 12 by bonding wires. An .alpha. ray shielding sheet 17 made of high purity (preferably exceeding 5-9) silicon several 100.mu .m thick including the thickness of another adhesive layer 16 made of phosphorus silicide glass or lead glass etc. is bonded on the surface of active region of semiconductor chip 14 before or after wire bonding process while a ceramics—made insulating cap 18 is bonded on the base 10 through the intermediary of a low melting point glass layer 19.

58/3, AB/1 (Item 1 from file: 350) DIALOG(R) File 350: Derwent WPIX (c) 2002 Thomson Derwent. All rts. reserv. 013430047 WPI Acc No: 2000-601990/200057 XRAM Acc No: C00-180156 Production of additive-loaded fibers or film, e.g. for making sintered, hollow inorganic membranes, involves co-extruding additive-containing cellulose solutions in amine N-oxide and coagulating combined extrudate Patent Assignee: OSTTHUERINGISCHE MATERIALPRUEFGESELLSCHA (OSTT-N) Inventor: SCHULZE T; TAEGER E; VORBACH D Number of Countries: 023 Number of Patents: 002 Patent Family: Patent No Kind Date Applicat No Kind Date Week WO 200053833 Al 20000914 WO 2000DE552 Α 20000224 200057 B C1 20010118 DE 1010012 DE 19910012 Α 19990308 200104 Priority Applications (No Type Date): DE 1010012 A 19990308 Patent Details: Patent No Kind Lan Pg Main IPC Filing Notes WO 200053833 A1 G 26 D01F-008/02 Designated States (National): CA CN JP KR US Designated States (Regional): AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE DE 19910012 C1 D01F-002/02 Abstract (Basic): WO 200053833 A1 Abstract (Basic): NOVELTY - The production of shaped products, especially filaments or film, from polysaccharides or their derivatives or polyvinyl alcohol involves making at least two solutions of the polymer in amine N-oxide-containing solvent, at least one of which also contains finely-dispersed additive(s), co-extruding the solutions and then coagulating the combined extrudate as usual. USE - For the production of shaped products, especially fibers or film, useful as special materials based on selected additives, e.g. porous, multilayer, inorganic hollow membranes, multilayer membrane

catalyst supports, ionic conductors etc.

ADVANTAGE - Enables the production of solid or hollow
multi-component fibers or film etc. with very different contents of
additives selected to give a wide range of special properties in the
final sintered product.

reactors, ceramic matrix composites, conductive multi-component fibers,

DESCRIPTION OF DRAWING(S) - Axial section of a 3-component round die for co-extrusion of additive-containing polymer solutions.

central cylindrical channel (1) annular channels (2, 3) pp; 26 DwgNo 1/2

58/3, AB/2 (Item 2 from file: 350) DIALOG(R) File 350: Derwent WPIX (c) 2002 Thomson Derwent. All rts. reserv. 012990101 WPI Acc No: 2000-161953/200015 XRAM Acc No: C00-050822 Fast-curing, condensation-crosslinked silicone material for adhesive or sealant applications contains polysiloxane and amino-, oxime- or alkoxysilane crosslinker Patent Assignee: HEIDELBERGER BAUCHEMIE GMBH (HEID-N) Inventor: FUTSCHER M; LUFT W; PAHL H; WERNER L Number of Countries: 029 Number of Patents: 005 Patent Family: Kind Patent No Kind Date Applicat No Date DE 19832688 20000203 DE 1032688 19980721 200015 B A1 Α WO 200005309 20000203 WO 99EP4801 Α 19990708 200015 A1 EP 1102815 A1 20010530 EP 99934630 19990708 200131 Priority Applications (No Type Date): DE 1032688 A 19980721 Patent Details: Patent No Kind Lan Pg Main IPC Filing Notes DE 19832688 A1 6 C08L-083/04 Based on patent WO 200005309 EP 1102815 A1 G C08L-083/04 Abstract (Basic): DE 19832688 A1 Abstract (Basic): NOVELTY - An acid or basic neutral salt is used as the accelerator in a kit for the production of fast-curing, condensation-crosslinked silicone materials containing a diorganopolysiloxane with functional end groups, an amino-, oxime- or alkoxysilane crosslinker, an accelerator and optionally water, fillers, additives and pigments. DETAILED DESCRIPTION - A kit for the production of fast-curing, aminosilane-crosslinked silicone materials (optionally with fillers, suitable additives and pigments), containing (A) 100 parts by weight (pts. wt.) at least bifunctionally-terminated diorganopolysiloxane with a linear or branched chain comprising repeat units of formula -SiRlR20and at least two end groups Z; Z=H, OH, OR1, -OSiR3(NR4R5)2, -OSi(ON=CR4R5)3 or -OSi(OR3)3; R1, R2=optionally unsaturated 1-15C hydrocarbyl, possibly substituted with halogen or cyano groups; (B) 0.1-20 pts. wt. aminosilane crosslinker of formula R3y-Si(NR4R5)4-y or an oxime or alkoxy crosslinker of formula R3-Si(ONCR4R5)4-y or R3-Si(OR3)4-y, in which R3=H or optionally unsaturated hydrocarbyl or hydrocarbyloxy; R4, R5=H and/or optionally unsaturated 1-15C aliphatic, cycloaliphatic or aromatic hydrocarbyl, optionally substituted with halogen or CN; y=0 or 1; (C) 0.1-20 pts. wt. of an acid or basic neutral salt as accelerator; and (D) 0-20 pts. wt. water. An INDEPENDENT CLAIM is also included for a process for the production of a sealant or adhesive composition by

mixing (A) with (B) and (C) with (D) and combining the two mixtures just before use.

USE - As a sealant or adhesive or as a molding material (claimed). Applications include bonding metals, glass and plastics, protective coatings for electrical insulation, encapsulating materials for electrical and electronic components, impression materials and elastomer moldings.

58/3,AB/5 (Item 5 from file: 350) DIALOG(R)File 350:Derwent WPIX

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008491255

WPI Acc No: 1990-378255/199051

XRAM Acc No: C90-164750 XRPX Acc No: N90-288245

Anhydrite binder for mineral fibres etc. - used in forming heat- or

sound-insulating coating by spraying

Patent Assignee: SAID H (SAID-I)

Inventor: SAID H; SAID P

Number of Countries: 001 Number of Patents: 001

Patent Family:

Patent No Kind Date Applicat No Kind Date Week FR 2646416 A 19901102 FR 895727 A 19890428 199051 B

Priority Applications (No Type Date): FR 895727 A 19890428

Abstract (Basic): FR 2646416 A

Binder (I) for mineral fibres or other **insulating** prods. for forming **insulating** coating by spraying comprises anhydrite (II).

(I) pref. contains nonionic and/or anionic surface-active agents. (I) pref. contains very finely divided insol. fillers, pigments, and water-sol, or water-insol. colourants. Fillers pref. have particle dia. 25-100 microns and specific surface more than 10 sq. /g, (I) contg. 2-30, partic. 2-10, kg such filler per 100 kg coating. (I) contains water-repellents, resins, setting accelerators, swelling agents, and plasticising air entrainers. (I) contains up to 10, partic. 0.05-2, kg salt of fatty acid as water-repellent.

USE/ADVANTAGE - For forming **insulation** against heat or sound. (I) adheres well and is thixotropic, coating has good appearance, shows no cracking, is waterproof, and is less dense, hence of lower wt., than coatings obtd. using cement and/or lime.

58/3,AB/6 (Item 6 from file: 350) DIALOG(R)File 350:Derwent WPIX (c) 2002 Thomson Derwent. All rts. reserv. 004155697 WPI Acc No: 1984-301236/198449

XRAM Acc No: C84-128235

XRPX Acc No: N84-224594

Polyolefin electrical insulation contg. adsorbent for heavy metal

ions - or ion exchange binder, reducing water treeing

Patent Assignee: SIEMENS AG (SIEI )

Inventor: HENKEL H J; MULLER N; HENKEL H; MUELLER N Number of Countries: 018 Number of Patents: 014

Patent Family:

Patent No Kind Date Applicat No Kind US 4623755 A 19861118 US 85775705 A 19850913 198649 EP 127052 В 19891004 198940

Priority Applications (No Type Date): DE 3318988 A 19830525

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

DE 3318988 15 Α

EP 127052 A G

Designated States (Regional): AT BE CH DE FR GB IT NL SE

Abstract (Basic): EP 127052 A

1. Polyolefine-based electrical insulations, more particularly in the case of cables and leads, for medium and high voltage from approximately 10 kV having an additive to retard water trees, characterized in that they contain as an additive in homogeneous distribution 0.05 to 10% by weight, as compared with the total weight, of a substance, which is active in adsorbing heavy metal ions or which binds heavy metal ions by ion exchange, having a particle size of up to 50 microns or an agglomerate size of up to 100 microns.

(6pp)

DE 3318988 A

An electrical insulation based on polyolefins contains 0.05-10 wt.% of an active adsorbent for heavy metal ions or a substance which binds heavy metal ions in ion-exchange; the particle size of the additive is up to 50 microns, or the agglomerate size is up to 100 microns.

The additive is esp. pyrogenic and/or pptd. silica, alumina and alumina hydrate with high surface activity, and/or Al silicate. The additive may be a synthetic prod.. The amt. is partic. 0.1-4 (0.5-2) wt.%. The particle size is esp. up to 20 microns. The additive may be incorporated in the polyolefin with a phlegmatising agent, pref. as a paste.

Abstract (Equivalent): US 4623755 A

Insulated electrical conductor comprises polyolefin insulating compsn. contg. 0.1-4 wt.% homogeneously distributed silica, alumina (hydrate) or Al silicate which is absorption active for heavy metal ions or which binds heavy metal ions in an ion exchange and which has agglomerate size up to 100 micron.

Pref. the compsn. contains 0.5-2 wt.% pyrogenic and/or pptd. silica

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or Al oxide (hydrate) with large active surface or Al silicate, any of which may be prepd. synthetically.

USE/ADVANTAGE - For cables and wires, having medium and high voltages e.g. 10 kV or above. Formation of water trees in the insulating compsn. is prevented.

STIC-EIC 2800 CP4-9C18 Irina Speckhard 308-6559

58/3, AB/7 (Item 7 from file: 350)

DIALOG(R) File 350: Derwent WPIX

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002520205

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WPI Acc No: 1980-38234C/198021

High compressive strength shaped articles - comprising homogeneously arranged inorganic solid particles and larger densely packed particles Patent Assignee: DENSIT AS (DENS-N); AALBORG AS (AALB-N); BACHE H H

(BACH-I); AALBORG PORTLAND CEMENT FAB AS (AALB-N); DENSIT A/S (DENS-N)

Inventor: BACHE H H

Number of Countries: 021 Number of Patents: 017

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week	
WO 8000959	A	19800515				198021	В
EP 10777	Α	19800514				198021	
NO 7903532	A	19800623				198029	
US 5234754	A	19930810	US 80195422	Α	19800624	199333	
			US 83470628	A	19830228		
			US 86880332	A	19860624		
			US 88243157	А	19880909		

Priority Applications (No Type Date): DK 792976 A 19790713; DK 784924 A 19781103

Patent Details:

Patent No Kind Lan Pg Main IPC Filing Notes

US 5234754 A 28 B32B-018/00 Cont of application US 80195422 Cont of application US 83470628

Cont of application US 86880332

Abstract (Basic): WO 8000959 A

A shaped article having a coherent matrix comprises (A) homogeneously arranged inorganic solid particles of size 50 angstroms – 0.5 mu; (B) densely packed solid particles of size 0.5-100 mu, which are at least one order of magnitude larger than the particles (A); and opt. (C) additional bodies having at least one dimension which is at least one order of magnitude larger than the particles (A). Particles (A) are homogeneously distributed in the void vol. between particles (B).

Bodies (C) are Portland cement.

The article can be, e.g. an in situ cast oil well wall, duct of fissure filling, sheet, panel or tile of thin-walled plane or corrugated shape, anticorrosion protecting cover applied on steel and concrete parts, pipe, tube, electrically **insulating** part, nuclear shielding or container.

Abstract (Equivalent): EP 10777 B

A process for preparing a shaped article, the process comprising combining A) inorganic solid silica dust particles of a size of from 50 angstrom to 0.5 mu.m, and B) solid particles having a size of 0.5-100 mu.m and being at least one order of magnitude larger than the respective particles stated under A), at least 20% by weight

Composite material for producing a shaped article consists of homogeneously arranged in organic solid particles, 50 Angstrom - 0.5 mu in size, arranged in the voids between densely packed solid particles,  $0.5-100~\mathrm{mu}$  in size, in a proportion of  $0.1-50~\mathrm{vol.}\%$ .

103,

Surface active agent ensures homogeneous distribution and fluidity while liq. fills voids. Pref. inorganic particles are ultra-fine silica particles, dispersed in Portland cement particles.

STIC-EIC 2800 CP4-9C18 Irina Speckhard 308-6559

58/3, AB/8 (Item 8 from file: 347)

DIALOG(R) File 347: JAPIO

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05425727

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MAKE-UP COSMETIC

PUB. NO.: 09-040527 [JP 9040527 A] PUBLISHED: February 10, 1997 (19970210)

INVENTOR(s): YOSHIDA MASASHI

FUKUI HIROSHI

APPLICANT(s): SHISEIDO CO LTD [000195] (A Japanese Company or Corporation),

JP (Japan)

APPL. NO.: 07-210956 [JP 95210956] FILED: July 27, 1995 (19950727)

#### **ABSTRACT**

PROBLEM TO BE SOLVED: To obtain a new make-up cosmetic with the improved compatibility with skin, free from offensive odor peculiar to protein by formulating a wool and or hair component into the original cosmetic.

SOLUTION: Wool and/or the hair are finely ground to <=100.mu.m particle size, and s-cyanoethylated to remove insoluble cuticles. The resultant hydrophilic s-cyanoethylated keratin powder is formulated into the original cosmetic preferably at 1-95wt.% to the whole weight of the make-up cosmetic. The scyanoethylated keratin is intrinsically safe for human bodies because it is keratin protein, and the make-up cosmetic which contains the s-cyanoethylated keratin has also high safety to the skin because the cosmetic contains no or scarce surface-active agent. In addition, this make-up cosmetic is excellent in transparency and thermal insulation.

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58/3,AB/9 (Item 9 from file: 347) DIALOG(R)File 347:JAPIO (c) 2002 JPO & JAPIO. All rts. reserv.

03646595 ELECTROVISCOUS FLUID

PUB. NO.: 04-011695 [JP 4011695 A] PUBLISHED: January 16, 1992 (19920116)

INVENTOR(s): MURAKAMI KAKUJI

KURAMOTO SHINICHI NAGAI KIYOFUMI

APPLICANT(s): RICOH CO LTD [000674] (A Japanese Company or Corporation), JP

(Japan)

APPL. NO.: 02-115388 [JP 90115388] FILED: May 01, 1990 (19900501)

JOURNAL: Section: C, Section No. 930, Vol. 16, No. 156, Pg. 148, April

16, 1992 (19920416)

# ABSTRACT

PURPOSE: To increase shearing stress obtained when an electric field is applied and decrease current density by dispersing or suspending specific particles in an electrically **insulating** liquid.

CONSTITUTION: Particles, containing a surface active agent but being substantially free from water, having a dissociative functional group, such as -COOM, -SO(sub 3)M, -OM, -SM, -(R(sub 1), R(sub 2), R(sub 3))NX or -(R(sub 1), R(sub 2), R(sub 3))PX(wherein M is H, an alkali metal, an ammonium or a phosphonium; R(sub 1), R(sub 2), R(sub 3) are each H or a (substituted) alkyl; and X is an element or functional group capable of forming an anion, such as halogen) in the molecule and having a particle size of 0.1-100.mu .m, are dispersed or suspended in an electrically insulating liquid, that is a liquid which has been used as an electroviscous fluid giving the Winslow effect.

58/3,AB/10 (Item 10 from file: 347) DIALOG(R)File 347:JAPIO

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02752029

ANTISTATIC LAMINATED METAL PLATE

PUB. NO.: 01-049629 [JP 1049629 A] PUBLISHED: February 27, 1989 (19890227)

INVENTOR(s): SAEKI KATSUHIRO

TAKIZAWA KATSUHIKO

APPLICANT(s): NIPPON STEEL METAL PROD CO LTD [000683] (A Japanese Company

or Corporation), JP (Japan)

RIKEN VINYL KOGYO KK [470163] (A Japanese Company or

Corporation), JP (Japan)

APPL. NO.: 62-205234 [JP 87205234] FILED: August 20, 1987 (19870820)

JOURNAL: Section: M, Section No. 833, Vol. 13, No. 237, Pg. 102, June

05, 1989 (19890605)

# ABSTRACT

PURPOSE: To decrease the self static build-up developed by vibration and friction, and rapidly decrease and eliminate inflowing static electricity by providing an earthing point on an antistatic layer by a method wherein the antistatic layer is provided through an electrical **insulating** layer on a metal base.

CONSTITUTION: A metal base 1, which is a steel plate galvanized 2 and then chromate- treated 3, is used so as to provide an antistatic layer 5 through an adherent electrical insulating layer 4 onto the base 1. In order to form the electrical insulating layer 4 onto the metal base 1, electrical insulating adhesive is applied onto the base. As the electrical insulating adhesive, adherent resin, which has functional groups and does not contain electrically conductive material, such as acrylic resin, epoxy resin, modified vinyl resin and the like are preferable. The antistatic layer 5 is formed by adding antistatic function to the resin by blending antistatic agent with the resin. As the resin, polyolefin resin, acrylic resin, polyester resin, polyamide resin, polyvinyl chloride resin or the like is exampled. The above-mentioned resin, to which the antistatic agent such as carbon powder, copper powder, powder, surface active agent, electrically metal other conductive plasticizing agent or the like is added, is applied onto the electrical insulating layer 4. The particle diameter of the antistatic agent used is normally 100.mu.m or less.

58/3,AB/11 (Item 11 from file: 347) DIALOG(R)File 347:JAPIO (c) 2002 JPO & JAPIO. All rts. reserv.

02597067

THIN-FILM TRANSISTOR ARRAY

PUB. NO.: 63-213967 [JP 63213967 A] PUBLISHED: September 06, 1988 (19880906)

INVENTOR(s): TERAO NORIYUKI
INO MASUMITSU
HIROI MASAKI
ABE SHUYA

APPLICANT(s): RICOH CO LTD [000674] (A Japanese Company or Corporation), JP

(Japan)

RICOH RES INST OF GEN ELECTRON [488199] (A Japanese Company

or Corporation), JP (Japan)

APPL. NO.: 62-048079 [JP 8748079] FILED: March 03, 1987 (19870303)

JOURNAL: Section: E, Section No. 700, Vol. 13, No. 2, Pg. 86, January

06, 1989 (19890106)

# ABSTRACT

PURPOSE: To prevent the stepped disconnection of a metallic electrode wiring and current leakage among said wiring and a source and a drain by forming an active layer region shaping a channel for a thin-film transistor by a polySi thin-film or an a-Si:H thin-film and forming the active layer region into a recessed section shaped onto a substrate surface so that the upper surface of the active layer region is conformed to the substrate surface.

CONSTITUTION: A recessed section 9 in the same area and the same depth as an active layer region are shaped to an <code>insulating</code> substrate 11 consisting of quartz, pyrex, etc. It is preferable that the recessed section 9 is formed to the rectangle of one side of 20-100.mu.m and depth is brought to 1000 angstroms or more. The recessed sections 9 are shaped only by the same number as the number of the active layer regions to be formed onto the <code>insulating</code> substrate 11. An active layer 5 composed of poly Si or a-Si:H is shaped into the recessed section 9 so that the upper <code>surface</code> of the <code>active</code> layer 5 is conformed to the upper surface of the <code>insulating</code> substrate 11. A gate oxide film 4, a gate electrode 6 a source 2 and a drain 3 are formed, and an inter-layer <code>insulating</code> film 7 shaped through a decompression CVD method is laminated onto these film and electrode and source and drain. A metallic electrode wiring 8 is formed onto a contact hole shaped to the inter layer <code>insulating</code> film 7.

58/3,AB/14 (Item 14 from file: 347) DIALOG(R)File 347:JAPIO (c) 2002 JPO & JAPIO. All rts. reserv.

00830512

MANUFACTURE OF INSULATED COIL

PUB. NO.: 56-150812 [JP 56150812 A] PUBLISHED: November 21, 1981 (19811121)

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APPL. NO.: 55-053843 [JP 8053843] FILED: April 22, 1980 (19800422)

JOURNAL: Section: E, Section No. 96, Vol. 06, No. 32, Pg. 15, February

26, 1982 (19820226)

# ABSTRACT

PURPOSE: To obtain the **insulated** coil of simple manufacturing operation having superior mechanical, electrical and thermal characteristics by a method wherein after a polyamide paper being made to contain a synthetic resin dispersion liquid is wound around a coil conductor, formation is performed by heating with pressure.

CONSTITUTION: The synthetic resin like polyester resin, epoxyester resin, polyester imide resin or polyester amide imide resin, etc., is pulverized by a jet mill, etc., to form the particle having the average diameter of 100.mu.m or less, for example, and thus obtained powder is made to disperse uniformly in water containing an anionic or a cationic surface active agent, and thus obtained dispersion liquid is made to be contained in a glass fiber. After the coil conductor is wound around with the polyamide paper made by mixing thus obtained wet paper type glass fiber, it is inserted in a metal mold to form by heating with pressure. Accordingly the insulated coil having superior electrical, mechanical and thermal characteristics can be obtained.

61/3, AB/1 (Item 1 from file: 347)

DIALOG(R) File 347: JAPIO

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06113020

ELECTRONIC PART HAVING BUMP AND MOUNTING STRUCTURE THEREOF

PUB. NO.: 11-054553 [JP 11054553 A] PUBLISHED: February 26, 1999 (19990226)

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APPLICANT(s): DENSO CORP

APPL. NO.: 09-204729 [JP 97204729] FILED: July 30, 1997 (19970730)

#### ABSTRACT

PROBLEM TO BE SOLVED: To prevent a defective contact of an electronic part and a mounting substrate by preventing the stripping of a **solder** bump from an electrode.

SOLUTION: An outermost surface of a circuit wiring 6 formed on the surface of an interposer 5 bonded to a solder bump 9 is formed of ductility metal. That is to say, when the junction interface of the circuit wiring 6 and the solder bump 9 is formed of an alloy layer comprising metal having ductility, the alloy at the junction interface of the circuit wiring 6 and the solder bump 9 is not broken by stress, and the stripping of the solder bump 9 from the junction interface can be prevented. Thus, the defective contact between a BGA(ball grid array) package 1 and a multi-layer printed wiring substrate 3 can be prevented. In detail, in the circuit wiring 3, the part in junction with the solder bump 9 is constituted of copper, tin or palladium.

61/3,AB/2 (Item 1 from file: 351) DIALOG(R) File 351: Derwent WPI (c) 2002 Thomson Derwent. All rts. reserv. 012994734 WPI Acc No: 2000-166586/200015 XRPX Acc No: N00-125081 Solder bump and pad electrode connection structure in ball grid array - has paste made of tungsten or molybdenum filled in hole from which wiring layer is extended to connect first layer of pad electrode with electric component Patent Assignee: NIPPONDENSO CO LTD (NPDE ) Number of Countries: 001 Number of Patents: 001 Patent Family: Patent No Kind Date Applicat No Kind Date Week JP 2000022070 A 20000121 JP 98182942 Α 1998062 200015 B Priority Applications (No Type Date): JP 98182942 A 19980629 Patent Details: Patent No Kind Lan Pg Main IPC Filing Notes JP 2000022070 A 8 H01L-025/00 Abstract (Basic): JP 2000022070 A NOVELTY - The laminated green sheets of an interposer (1), consists of a hole to connect the surfaces (la,lb). A paste made of tungsten or molybdenum is filled in the hole. A wiring layer from the hole connects the layer (9a) of pad electrode to the electric components (2,4). DETAILED DESCRIPTION - A semiconductor chip (2), an electric component (3) and a thick film resistor (4) are formed on the surface (1a) of an interposer (1). A pad electrode (9) formed on surface (1b) is electrically connected with the electric components (2-4). The pad electrode consists of two layers (9a,9b) made of tungsten or molybdenum and copper plating, respectively. A solder bump (10) joined to the pad electrode electrically connects the electric component to the exterior circuit. USE - In ball grid array (BGA) and multi-chip module (MCM). ADVANTAGE - The durability of solder junction is increased. DESCRIPTION OF DRAWING(S) - The figure shows explanatory diagram of multi-chip module. (1) Interposer; (1a,1b) Interposer surfaces; (2-4) Electronic components; (9) Pad electrode; (9a,9b) Layers; (10) Solder bump.

1. 4

65/3,AB/1 (Item 1 from file: 351) DIALOG(R) File 351: Derwent WPI (c) 2002 Thomson Derwent. All rts. reserv. 009122170 WPI Acc No: 1992-249607/199230 XRAM Acc No: C92-111392 XRPX Acc No: N92-190694 Adhesive for reflow soldering and encapsulation of flip chip IC(s) - comprising thermosetting resin pref. epoxy or polyester, with fluxing agent pref. malic acid and curing agent Patent Assignee: MOTOROLA INC (MOTI ) Inventor: PAPAGEORGE M V; PENNISI R W Number of Countries: 002 Number of Patents: 003 Patent Family: Patent No Kind Applicat No Date Kind Date Week 19900927 19920707 US 90588888 US 5128746 A A 199230 B 19921006 JP 91272090 A 19910924 JP 4280443 Α 199246 JP 2589239 B2 19970312 JP 91272090 A 19910924 199715 Priority Applications (No Type Date): US 90588888 A 19900927 Patent Details: Patent No Kind Lan Pg Main IPC Filing Notes A 6 H01L-023/14 US 5128746

JP 4280443 6 H01L-021/60 Α

JP 2589239 В2 6 H01L-021/60 Previous Publ. patent JP 4280443

# Abstract (Basic): US 5128746 A

A thermally curable adhesive is claimed, which is used for re-flow soldering of an electrical component and a substrate, the adhesive comprising (A) a thermoset resin (pref. an epoxy or polyester); (B) a fluxing agent in sufficient amt. to remove oxide coatings from the electrical component or substrate (pref. a dicarboxylic acid of formula HOOC-CH2-CRH-COOH (I); and (C) a curing agent acting on heating. R = an electron-withdrawing gp., pref. F, Cl, Br, I, S, OH, CN or benzyl.

Also claimed is an assembly comprising (1) an electrical component with a no. of electrical terminations, each including a solder bump (240); (2) a substrate (200) having terminations corresp. to the terminations of the above component; and (3) an adhesive (220) contg. components (A)-(C) as above which removes oxide coatings from the component and substrate terminations.

USE/ADVANTAGE - The adhesive is esp. useful in encapsulating flip chip integrated circuits; it ensures complete coverage of the die surface and allows max. use of available substrate area. The fluxing agent in the adhesive coats the solder bumps (240) and the metallisation pattern (210) and the meniscus (260) provides a continuous seal around the device periphery to protect the active surface from environmental contamination.